MP87L85

Low Voltage CMOS
8-Bit High Speed
Analog-to-Digital Converter

March 1998-3

FEATURES

- 3.3 Volt Operation
- 8-Bit Resolution
- DNL = ±1/2 LSB, INL = ±1 LSB (typ)
- Internal S/H Function
- V_{IN} DC Range: 0 V to V_{DD}
- V_{REF} DC Range: 1 V to V_{DD}
- Low Power: 25 mW typ. (excluding reference)
- Latch-Up Free

APPLICATIONS

- Digital Radio
- Cellular Telephones
- CCD's and Scanners
- Hand Held and Battery Powered Data Acquisition

GENERAL DESCRIPTION

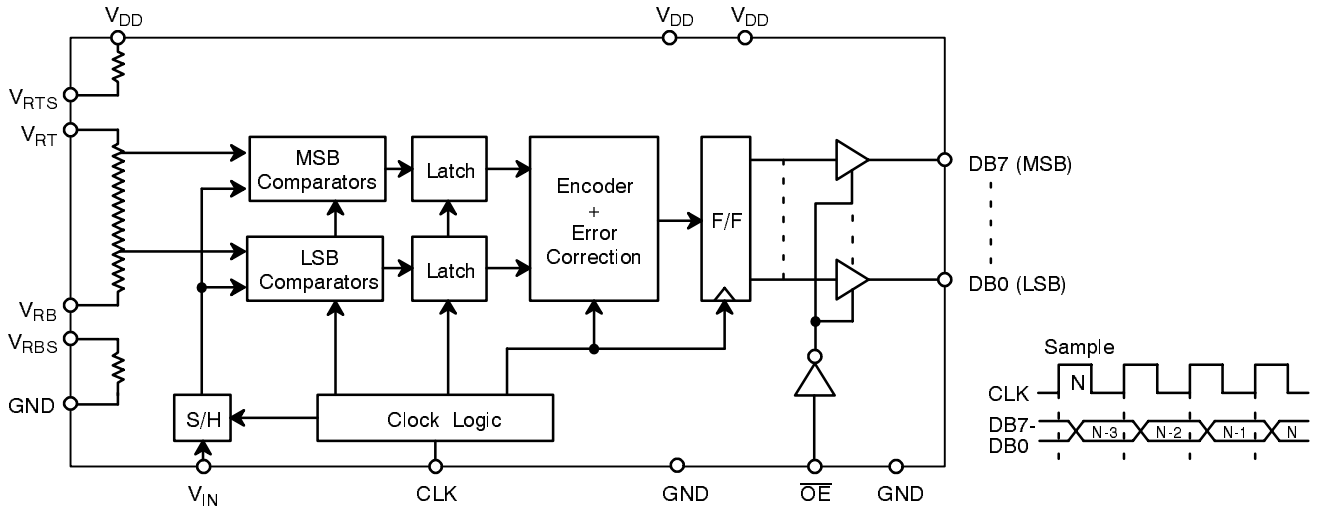
The MP87L85 is an 8-bit Analog-to-Digital Converter that operates at 3.3 V. Designed using an advanced CMOS process, this part offers excellent performance, low power consumption and latch-up free operation.

This device uses a two-step flash architecture to maintain low power consumption at high conversion rates. The input circuitry of the MP87L85 includes an on-chip S/H function which allows the user to digitize analog input signals between GND and V_{DD}. Careful design and chip layout have achieved a low analog input capacitance. This reduces "kickback" and eases the requirements of the buffer/amplifier used to drive the MP87L85.

The designer can choose the internally generated reference voltages by connecting V_{RB} to V_{RBS} and V_{RT} to V_{RTS}, or provide external reference voltages to the V_{RB} and V_{RT} pins. The internal reference generates 0.4 V at V_{RB} and 1.72 V at V_{RT}. Providing external reference voltages allows easy interface to any input signal range between AGND and AV_{DD}. This also allows the system to adjust these voltages to cancel zero scale and full scale errors, or to change the input range as needed.

The device operates from a single +3.3 V supply ±10%. Power consumption is 35 mW maximum at Fs = 10 MHz.

SIMPLIFIED BLOCK AND TIMING DIAGRAM



Rev. 3.00

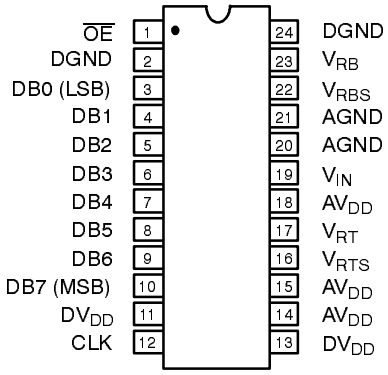
EXAR Corporation, 48720 Kato Road, Fremont, CA 94538 ◆ (510) 668-7000 ◆ (510) 668-7017

ORDERING INFORMATION

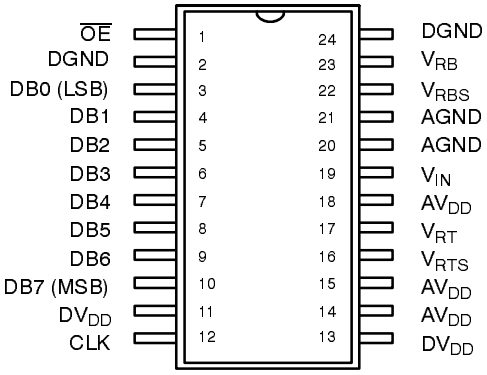
Package Type	Temperature Range	Part No.	DNL (LSB)	INL (LSB)
SOIC (EIAJ)	–40 to +85°C	MP87L85AR	±1/2	1 1/2
SOIC (Jedec)	–40 to +85°C	MP87L85AS	±1/2	1 1/2
Plastic Dip (0.300")	–40 to +85°C	MP87L85AN	±1/2	1 1/2

PIN CONFIGURATIONS

See Packaging Section for Package Dimensions



24 Pin PDIP (0.300")



24 Pin SOIC EIAJ (0.300") & Jedec (0.300")

PIN OUT DEFINITIONS

PIN NO.	NAME	DESCRIPTION
1	$\overline{OE}$	Output Enable
2	DGND	Digital Ground
3	DB0	Data Output Bit 0 (LSB)
4	DB1	Data Output Bit 1
5	DB2	Data Output Bit 2
6	DB3	Data Output Bit 3
7	DB4	Data Output Bit 4
8	DB5	Data Output Bit 5
9	DB6	Data Output Bit 6
10	DB7	Data Output Bit 7 (MSB)
11	DV_{DD}	Digital Power Supply
12	CLK	Sampling Clock Input

PIN NO.	NAME	DESCRIPTION
13	DV_{DD}	Digital Power Supply
14	AV_{DD}	Analog Power Supply
15	AV_{DD}	Analog Power Supply
16	V_{RTS}	Generates 1.72 V if tied to V_{RT}
17	V_{RT}	Top Reference
18	AV_{DD}	Analog Power Supply
19	V_{IN}	Analog Input
20	AGND	Analog Ground
21	AGND	Analog Ground
22	V_{RBS}	Generates 0.4 V if tied to V_{RB}
23	V_{RB}	Bottom Reference
24	DGND	Digital Ground

ELECTRICAL CHARACTERISTICS TABLE

Unless Otherwise Specified: AV_{DD} = DV_{DD} = 3.3 V, FS = 6 MHz (50% Duty Cycle), V_{RT} = 2.5 V, V_{RB} = 0.5 V, T_A = 25°C

Parameter	Symbol	25°C Min	25°C Typ	25°C Max	Units	Test Conditions/Comments
KEY FEATURES						
Resolution		8			Bits	
Sampling Rate	FS	0.1		10	MHz	
ACCURACY (A Grade)[1]						
Differential Non-Linearity	DNL			±1/2	LSB	
Integral Non-Linearity	INL			1 1/2	LSB	Best Fit Line (Max INL – Min INL)/2
REFERENCE VOLTAGES						
Differential Ref. Voltage[3]	V_{REF}	1.0		AV_{DD}	V	$V_{REF} = V_{RT} - V_{RB}$
Ladder Resistance	R_L		350		Ω	
Ladder Temp. Coefficient	R_{TCO}		2000		ppm/°C	
Self Bias 1						
Short V_{RB} and V_{RBS}	V_{RB}		0.36		V	
Short V_{RT} and V_{RTS}	V_{RT}-V_{RB}		1.32		V	
Self Bias 2						
V_{RB} = AGND, Short V_{RT} and V_{RTS}	V_{RT}		1.52		V	
ANALOG INPUT						
Input Bandwidth (–1 dB)[4]	BW		5		MHz	
Input Voltage Range	V_{IN}	V_{RB}		V_{RT}	V	
Input Capacitance[5]	C_{IN}		16		pF	
Aperture Delay	t_{AP}		30		ns	
DIGITAL INPUTS						
Logical "1" Voltage	V_{IH}	2.5			V	
Logical "0" Voltage	V_{IL}			0.5	V	
DC Leakage Currents[6]	I_{IN}					V_{IN}=DGND to DV_{DD}
CLK			5		µA	
Input Capacitance			5		pF	
Clock Timing (*See Figure 1.*)[7]						
Clock Period	1/FS		100		ns	
High Pulse Width	t_{PWH}		50		ns	
Low Pulse Width	t_{PWL}		50		ns	
DIGITAL OUTPUTS						C_{OUT}=15 pF
Logical "1" Voltage	V_{OH}	2.5			V	I_{LOAD} = 1 mA
Logical "0" Voltage	V_{OL}			0.5	V	I_{LOAD} = 1 mA
3-state Leakage	I_{OZ}		10		µA	V_{OUT}=DGND to DV_{DD}
Data Valid Delay	t_{DL}		30		ns	
Data Enable Delay	t_{DEN}		35		ns	
Data 3-state Delay	t_{DHZ}		17		ns	

ELECTRICAL CHARACTERISTICS TABLE (CONT'D)

Description	Symbol	25°C Min	25°C Typ	25°C Max	Units	Conditions
POWER SUPPLIES						
Operating Voltage	V_{DD}	3	3.3	3.6	V	
Current	I_{DD}		6	12	mA	Does not include ref. current

Notes:

1 *Tester measures code transitions by dithering the voltage of the analog input (V_{IN}). The difference between the measured and the ideal code width (V_{REF}/256) is the DNL error (Figure 2.). The INL error is the maximum distance (in LSBs) from the best fit line to any transition voltage (Figure 3.). Accuracy is a function of the sampling rate (FS).*

2 *Guaranteed. Not tested.*

3 *Specified values guarantee functionality. Refer to other parameters for accuracy.*

4 *–1 dB bandwidth is a measure of performance of the A/D input stage (S/H + amplifier). Refer to other parameters for accuracy within the specified bandwidth.*

5 *See V_{IN} input equivalent circuit (Figure 4.). Switched capacitor analog input requires driver with low output resistance.*

6 *All inputs have diodes to DV_{DD} and DGND. Input DC currents will not exceed specified limits for any input voltage between DGND and DV_{DD}.*

7 *t_R, t_F should be limited to >5 ns for best results.*

8 *AGND & DGND pins are connected through the silicon substrate. Connect together at the package and to the analog ground plane.*

Specifications are subject to change without notice

ABSOLUTE MAXIMUM RATINGS (T_A = +25°C unless otherwise noted)[1, 2, 3]

V_{DD} to GND ..... 5.5 V
V_{RT} & V_{RB} ..... V_{DD} +0.5 to GND –0.5 V
V_{IN} ..... V_{DD} +0.5 to GND –0.5 V
All Inputs ..... V_{DD} +0.5 to GND –0.5 V
All Outputs ..... V_{DD} +0.5 to GND –0.5 V

Storage Temperature ..... –65 to +150°C
Lead Temperature (Soldering 10 seconds) ..... +300°C
Package Power Dissipation Rating @ 75°C
SOIC, PDIP ..... 850 mW
Derates above 75°C ..... 11 mW/°C

Notes:

1 *Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation at or above this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.*

2 *Any input pin which can see a value outside the absolute maximum ratings should be protected by Schottky diode clamps (HP5082-2835) from input pin to the supplies. All inputs have protection diodes which will protect the device from short transients outside the supplies of less than 100mA for less than 100µs.*

3 *V_{DD} refers to AV_{DD} and DV_{DD}. GND refers to AGND and DGND.*

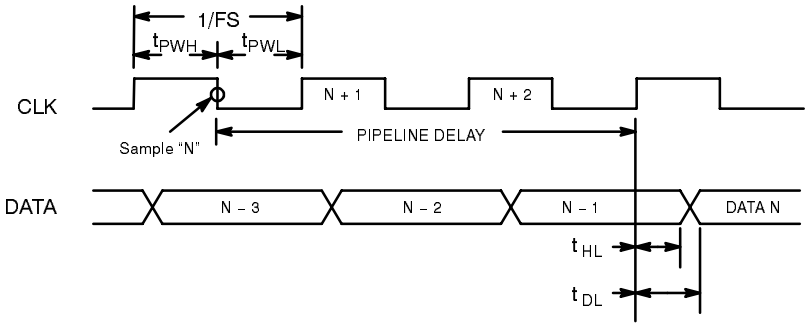
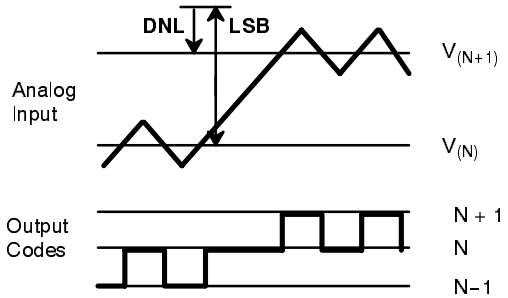


Figure 1. MP87L85 Timing Diagram



Code Width (N) = $V_{(N+1)} - V_{(N)}$
LSB = [$V_{RT} - V_{RB}$] / 256

$DNL_{(N)} = [V_{(N+1)} - V_{(N)}] - LSB$

Figure 2. DNL Measurement

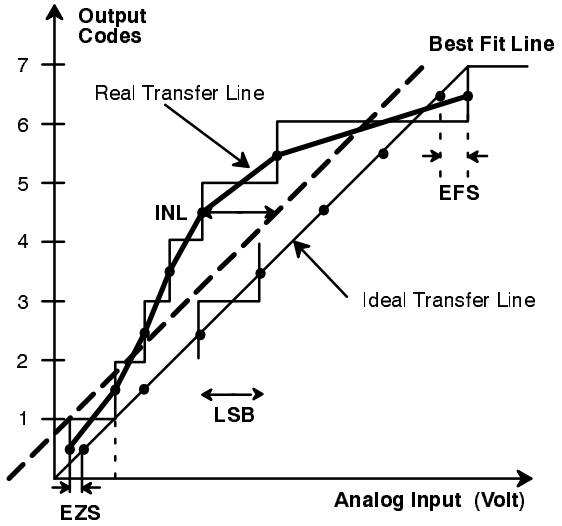


Figure 3. INL Error Calculation

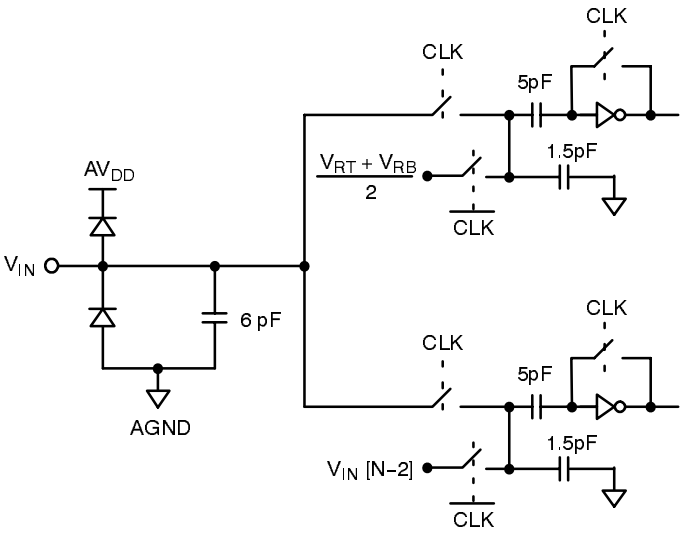


Figure 4. Equivalent Input Circuit

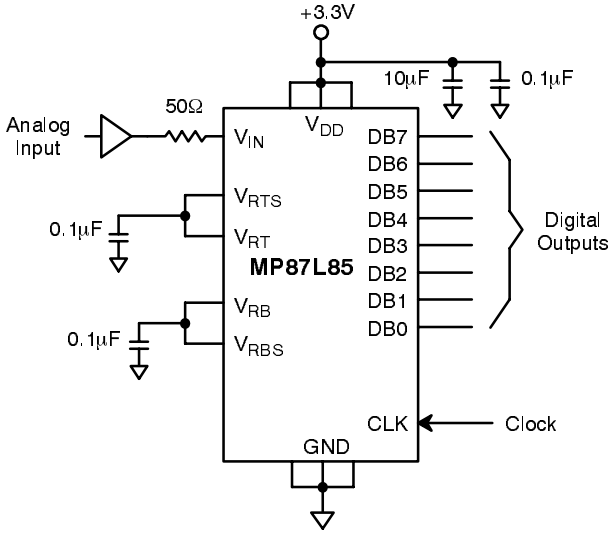


Figure 5. Typical Circuit Connections

APPLICATION NOTES

Signals should not exceed AV_{DD} +0.5V or go below AGND −0.5V or DV_{DD} +0.5 V or DGND −0.5 V. All pins have internal protection diodes that will protect them from short transients (<100μs) outside the supply range.

AGND and DGND pins are connected internally through the P-substrate. DC voltage differences between these pins will cause undesirable internal substrate currents.

The power supply (AV_{DD}) and reference voltage (V_{RT} & V_{RB}) pins should be decoupled with 0.1μF and 10μF capacitors to AGND, placed as close to the chip as possible.

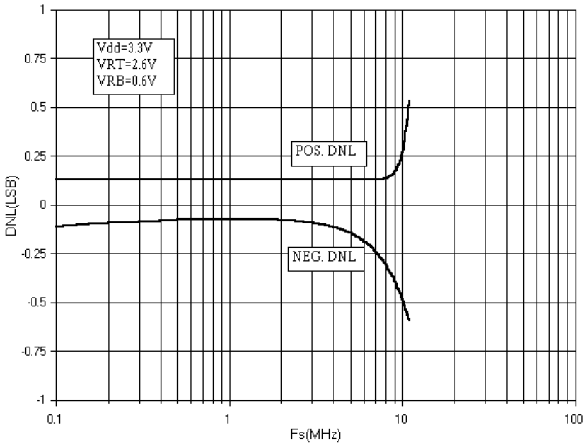
The digital outputs should not drive long wires or buses. The capacitive coupling and reflections will contribute noise to the conversion.

It is possible for the data valid delay (t_{DL}) to be equal to or greater than the high pulse width of the sampling clock (t_{PWH}). See *Figure 1.* This can cause timing related errors. For sample rates above 14 MSPS use only the rising edge of the sample clock (CLK) to latch data from the MP87L85 to other parts of the system.

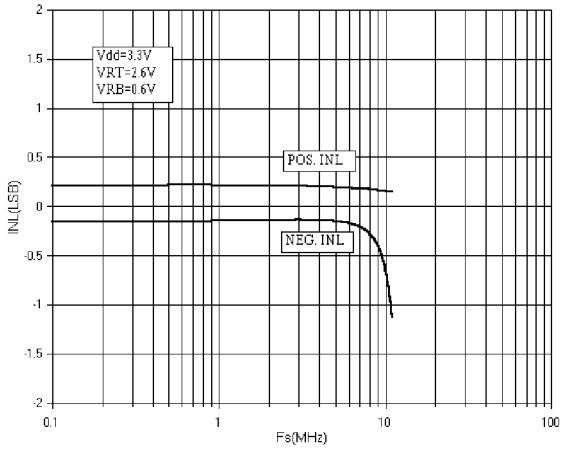
The reference can be biased internally by shorting V_{RT} to V_{RTS} and V_{RB} to V_{RBS}. This will generate 0.36 V at V_{RB} and 1.56 V at V_{RT} (see *Figure 5.).*

If the internal reference pins V_{RTS} and/or V_{RBS} are not used they should be left unconnected.

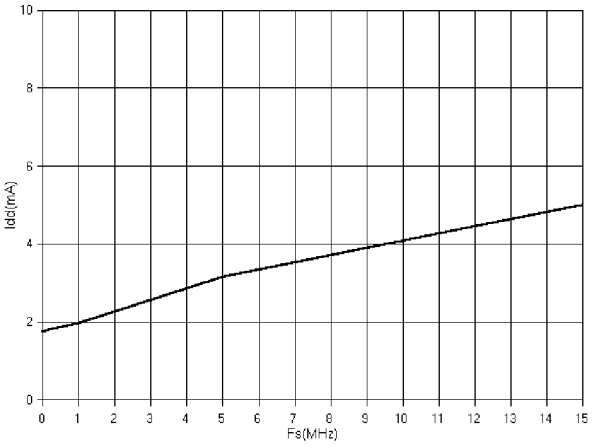
PERFORMANCE CHARACTERISTICS



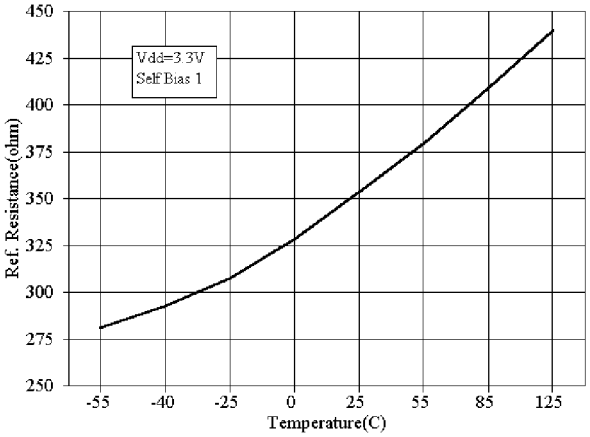
Graph 1. DNL vs. Sampling Frequency



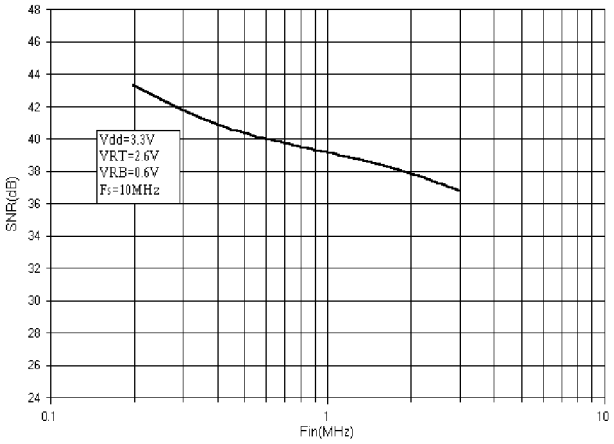
Graph 2. INL vs. Sampling Frequency



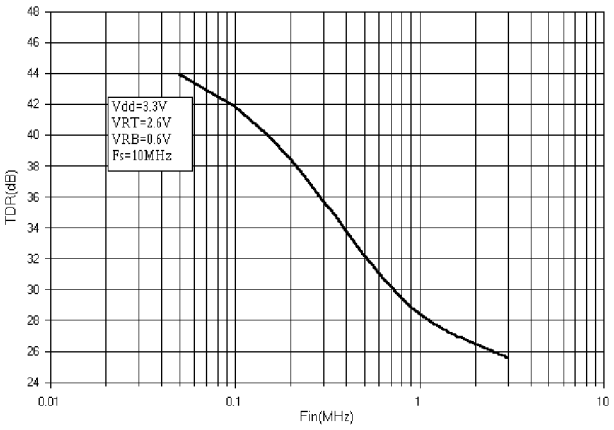
Graph 3. Supply Current vs. Sampling Frequency



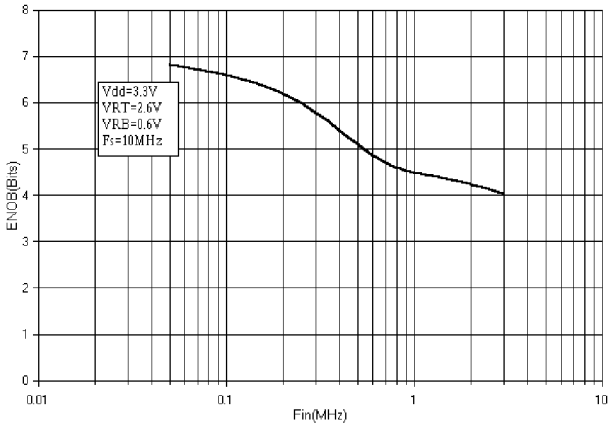
Graph 4. Reference Resistance vs. Temperature



Graph 5. SNR vs. Input Frequency



Graph 6. SINAD vs. Input Frequency



Graph 7. ENOB vs. Input Frequency